

H5N2802PF

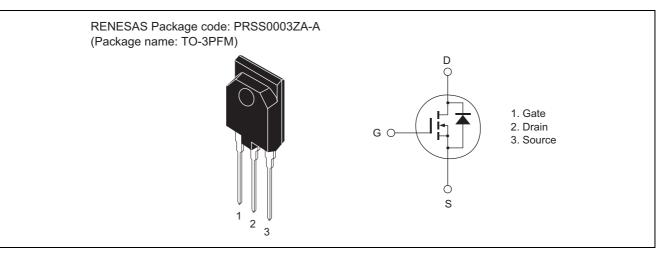
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1298-0200 Rev.2.00 Dec 12, 2008

Features

- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	280	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	25	А
Drain peak current	Note1 I _{D (pulse)}	100	А
Body-drain diode reverse drain current	I _{DR}	25	А
Body-drain diode reverse drain peak current	Note1 DR (pulse)	100	А
Avalanche current	I _{AP} ^{Note3}	13	А
Avalanche energy	E _{AR} ^{Note3}	10.2	mJ
Channel dissipation	Pch Note2	60	W
Channel to case thermal impedance	θch-c	2.08	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	۵°

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at $Tc = 25^{\circ}C$

3. STch = 25° C, Tch $\leq 150^{\circ}$ C



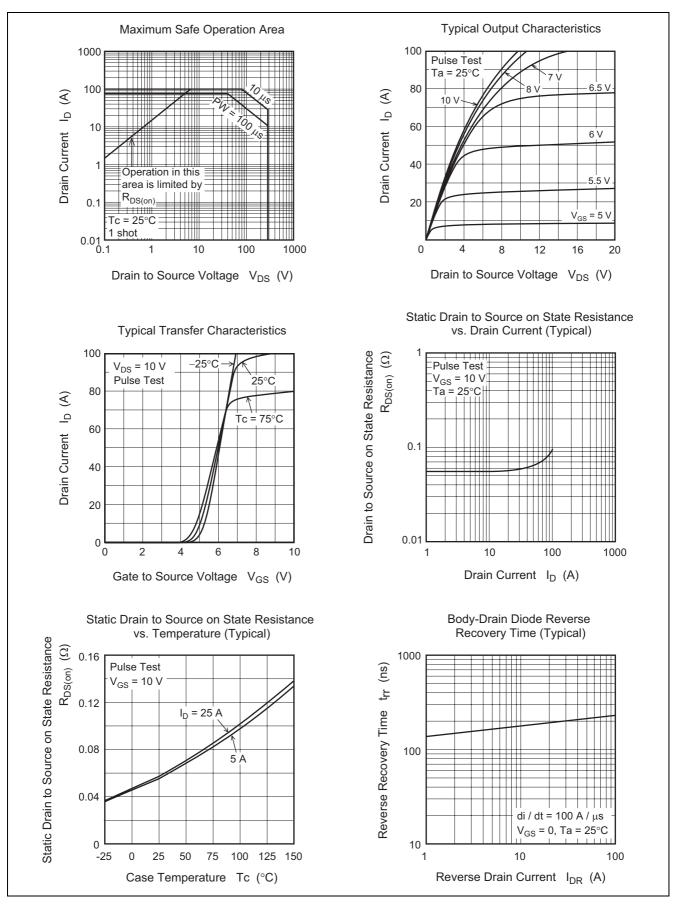
Electrical Characteristics

Item	Symbol	Min	Тур	Max	Unit	Test conditions	
Drain to source breakdown voltage	V _{(BR)DSS}	280	_		V	$I_D = 10 \text{ mA}, V_{GS} = 0$	
Zero gate voltage drain current	I _{DSS}	_	—	1	μΑ	$V_{DS} = 280 \text{ V}, V_{GS} = 0$	
Gate to source leak current	I _{GSS}		—	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$	
Gate to source cutoff voltage	V _{GS(off)}	3.0	_	4.0	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	
Forward transfer admittance	y _{fs}	15	27		S	$I_D = 12.5 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$	
Static drain to source on state	R _{DS(on)}		0.057	0.066	Ω	$I_D = 12.5 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$	
resistance							
Input capacitance	Ciss	—	3600		pF	$V_{DS} = 25 V, V_{GS} = 0,$ f = 1 MHz	
Output capacitance	Coss	—	450		pF		
Reverse transfer capacitance	Crss	_	32	_	pF		
Turn-on delay time	t _{d(on)}	_	50		ns	I_D = 12.5 A, V _{GS} = 10 V, R _L = 11.2 Ω, Rg = 10 Ω	
Rise time	tr	_	90		ns		
Turn-off delay time	t _{d(off)}	_	120		ns		
Fall time	t _f	_	75		ns		
Total gate charge	Qg	_	72		nC	$V_{DD} = 220 \text{ V}, V_{GS} = 10 \text{ V},$ $I_D = 25 \text{ A}$	
Gate to source charge	Qgs		18		nC		
Gate to drain charge	Qgd		24		nC		
Body-drain diode forward voltage	V _{DF}	_	0.88	1.40	V	$I_F = 25 \text{ A}, V_{GS} = 0^{Note4}$	
Body-drain diode reverse recovery time	t _{rr}		200		ns	$I_F = 25 \text{ A}, V_{GS} = 0,$	
Body-drain diode reverse recovery	Qrr	_	1.4	—	μC	di _F /dt = 100 A/µs	
charge							

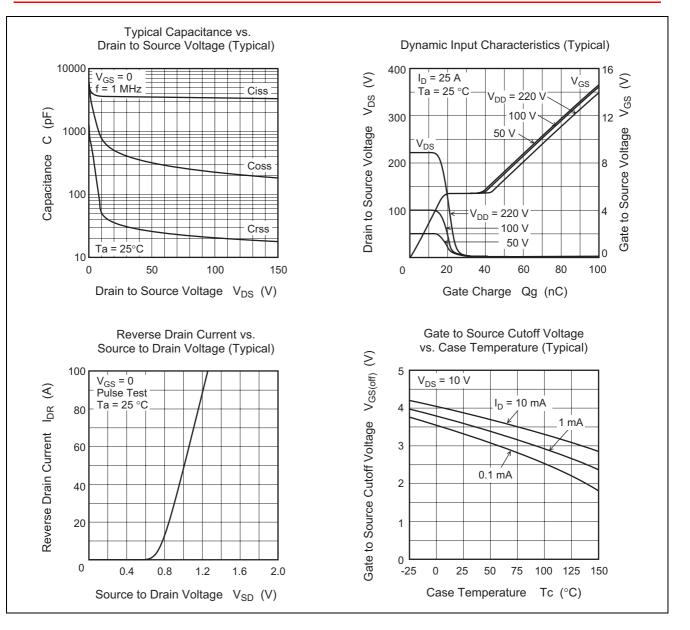
Notes: 4. Pulse test



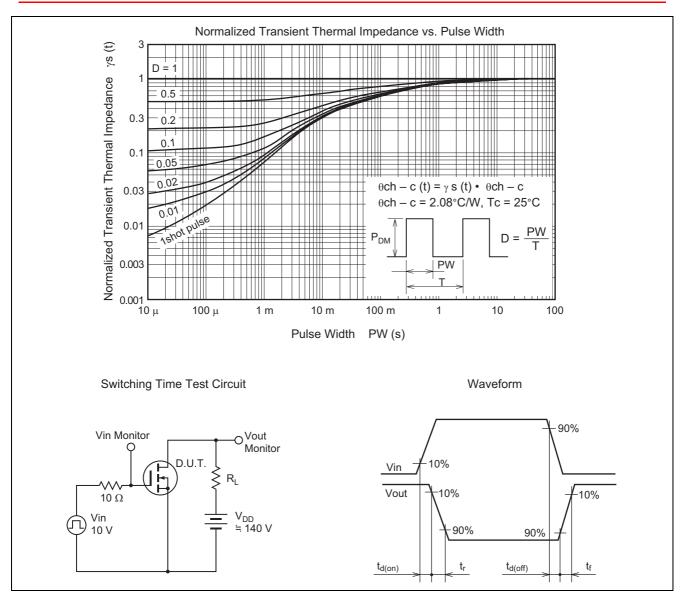
Main Characteristics



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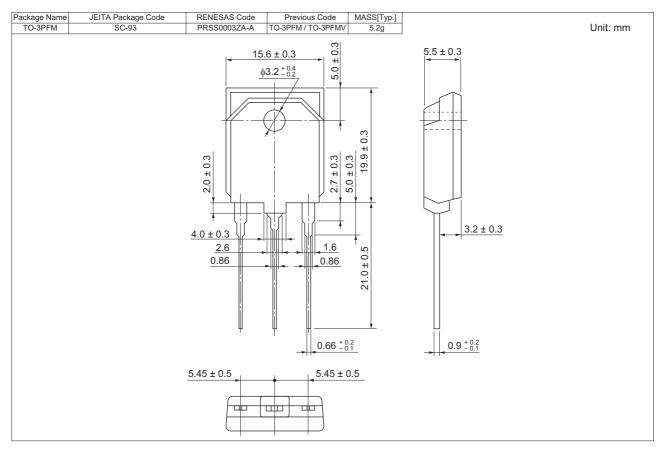








Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
H5N2802PF-E	360 pcs	Box (Tube)



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